



Product Overview

NTMS4816N: Power MOSFET 30V 11A 10mOhm Single N-Channel SO-8

For complete documentation, see the data sheet

Product Description

This is a 30 V N-Channel Power MOSFET.

Features

- Low Capacitance to Minimize Driver Losses
- Optimized Gate Charge to Minimize Switching Losses
- This is a Pb-Free Device
- Low $R_{DS(on)}$ to Minimize Conduction Losses

Applications

- Disk Drives
- DC-DC Converters
- Printers

Part Electrical Specifications

Product	Compliance	Status	Channel Polarity	Configuration	$V_{DS(BR)}$ Min (V)	V_{GS} Max (V)	$V_{GS(th)}$ Max (V)	I_D Max (A)	P_D Max (W)	$r_{DS(on)}$ Max @ $V_{GS} = 2.5$ V (m)	$r_{DS(on)}$ Max @ $V_{GS} = 4.5$ V (m)	$r_{DS(on)}$ Max @ $V_{GS} = 10$ V (m)	Q_g Typ @ $V_{GS} = 4.5$ V (nC)	Q_g Typ @ $V_{GS} = 10$ V (nC)	Q_{gd} Typ @ $V_{GS} = 4.5$ V (nC)	Q_{rr} Typ (nC)	C_{iss} Typ (pF)	C_{oss} Typ (pF)	C_{rss} Typ (pF)	Package Type
NTMS4816NR2G	Pb-free Halide free	Active	N-Channel	Single	30	20	3	11	2.04		16	10	9.2	18.3	3.8	9	1060	220	126	SOIC-8

For more information please contact your local sales support at www.onsemi.com

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